ΒΑΣΙΚΕΣ ΕΞΙΣΩΣΕΙΣ ΗΛΕΚΤΡΟΝΙΚΗΣ ΙΙΙ

Ζεύγος κοινού συλλέκτη - κοινής βάσης:

$$\begin{split} \frac{V_o}{V_{sig}} &= \frac{1}{2} \left(\frac{R_{in}}{R_{in} + R_{sig}} \right) (g_m R_L) \\ f_{P1} &= \frac{1}{2\pi \left(\frac{C_{\pi}}{2} + C_{\mu} \right) (R_{sig} \parallel 2r_{\pi})} \end{split} \qquad f_{P2} &= \frac{1}{2\pi C_{\mu} R_L} \qquad f_H \cong \frac{1}{\sqrt{\frac{1}{f_{P1}^2} + \frac{1}{f_{P2}^2}}} \end{split}$$

Ζεύγος κοινής πηγής - κοινής πύλης (κασκοδική συνδεσμολογία):

$$\begin{split} R_{out} &= r_{o2} + \left[1 + (g_{m2} + g_{mb2}) \, r_{o2}\right] r_{o1} \quad A_v = -A_0^2 \frac{R_L}{R_L + A_0 r_0} \qquad \qquad f_H \cong \frac{1}{2\pi \tau_H} \\ R_{gd1} &= (1 + g_{m1} R_{d1}) \, R_{sig} + R_{d1} \qquad \qquad \tau_H = R_{sig} \left[C_{gs1} + C_{gd1} \left(1 + g_{m1} R_{d1}\right)\right] + R_{d1} \left(C_{gd1} + C_{db1} + C_{gs2}\right) + \left(R_L \parallel R_{out}\right) \left(C_L + C_{gd2}\right) \end{split}$$

Ζεύγος κοινού εκπομπού - κοινής βάσης (κασκοδική συνδεσμολογία):

$$\begin{split} A_{M} &= -\frac{r_{\pi}}{r_{\pi} + r_{x} + R_{sig}} g_{m} \left(\beta r_{0} \parallel R_{L}\right) & R_{c1} &= r_{01} \parallel \left[r_{e2} \left(\frac{r_{o2} + R_{L}}{r_{o2} + R_{L}/(\beta_{2} + 1)} \right) \right] \\ R'_{sig} &= r_{\pi 1} \parallel \left(r_{x1} + R_{sig} \right) & \tau_{H} &= C_{\pi 1} R_{\pi 1} + C_{\mu 1} R_{\mu 1} + \left(C_{cs1} + C_{\pi 2} \right) R_{c1} + \left(C_{L} + C_{cs2} + C_{\mu 2} \right) \left(R_{L} \parallel R_{out} \right) \\ R_{\mu 1} &= R'_{sig} \left(1 + g_{m1} R_{c1} \right) + R_{c1} & f_{H} &\simeq \frac{1}{2\pi \tau_{H}} \end{split}$$

Τελεστικός ενισχυτής ΜΟS δύο βαθμίδων:

$$\begin{split} &A_{v} = -g_{m1} \left(r_{ds2} \parallel r_{ds4} \right) &g_{m1} = \sqrt{2 \mu_{p} C_{ox} \left(\frac{W}{L} \right)_{1} I_{D1}} = \sqrt{2 \mu_{p} C_{ox} \left(\frac{W}{L} \right)_{1} \frac{I_{bias}}{2}} \\ &R_{B} = \frac{2}{\sqrt{2 \mu_{n} C_{ox} \left(W/L \right)_{12} I_{B}}} \left(\sqrt{\frac{\left(W/L \right)_{12}}{\left(W/L \right)_{13}}} - 1 \right) &g_{mi} = g_{m12} \sqrt{\frac{I_{Di} \left(W/L \right)_{i}}{I_{B} \left(W/L \right)_{12}}} &g_{mi} = g_{m12} \sqrt{\frac{\mu_{p} I_{Di} \left(W/L \right)_{i}}{\mu_{n} I_{B} \left(W/L \right)_{12}}} \\ &C_{1} = C_{gd4} + C_{db4} + C_{gd2} + C_{gs6} &C_{2} = C_{db6} + C_{db7} + C_{gd7} + C_{L} \\ &\omega_{Z} = \frac{G_{m2}}{C_{C}} &\omega_{P1} = \frac{1}{C_{1} R_{1} + C_{2} R_{2} + C_{C} \left(G_{m2} R_{2} R_{1} + R_{1} + R_{2} \right)} \cong \frac{1}{R_{1} C_{C} G_{m2} R_{2}} \\ &\omega_{P2} = \frac{G_{m2} C_{C}}{C_{1} C_{2} + C_{C} \left(C_{1} + C_{2} \right)} &\omega_{t} = \left(G_{m1} R_{1} G_{m2} R_{2} \right) \omega_{P1} &\text{Epilopy in } C_{C} \text{ dotte } \omega_{t} < \omega_{Z} < \omega_{P2} \\ &\text{PSRR} = g_{mN} \left(r_{oP} \parallel r_{oN} \right) &\text{SR} \equiv \frac{d V_{out}}{dt} \bigg|_{\max} = \frac{I_{SS}}{C_{L}} \\ &\text{GB} = A_{v}(0) \cdot |p_{1}| = \left(g_{m1} g_{m2} R_{I} R_{II} \right) \cdot \left(\frac{1}{g_{m2} R_{I} R_{II} C_{C}} \right) = \frac{g_{m1}}{C_{C}} \\ &\text{PM} = \text{Arg} \left[AB \right] = \pm 180^{\circ} - \arctan \left(\frac{\omega}{|p_{1}|} \right) - \arctan \left(\frac{\omega}{|p_{2}|} \right) - \arctan \left(\frac{\omega}{|p_{2}|} \right) - \arctan \left(\frac{\omega}{|p_{2}|} \right) \end{split}$$

Για περιθώριο φάσης (PM) 45° και $Z\geqslant 10\cdot {\rm GB:}\; |p_2|\geqslant 1.22\cdot {\rm GB}$

Για περιθώριο φάσης (PM) 60° και $Z\geqslant 10\cdot {\rm GB}\colon |p_2|\geqslant 2.22\cdot {\rm GB}$

$$Z = \frac{1}{C_C \left(\frac{1}{g_{m2}} - R_Z\right)}$$

Τελεστικός ενισχυτής με είσοδο n-MOS $\max{(V_{in})} = V_{DD} - \sqrt{\frac{I_5}{\beta_3}} - \max{(|V_{T03}|)} + \min{(V_{T01})} \quad \min{(V_{in})} = V_{SS} + \sqrt{\frac{I_5}{\beta_1}} + \max{(V_{T01})} + V_{DS5_{sat}} \qquad V_{DS_{sat}} = \sqrt{\frac{2I_{DS}}{\beta}}$

Τελεστικός ενισχυτής με είσοδο p-MOS

$$\max{(V_{in})} = V_{DD} - \sqrt{\frac{I_5}{\beta_1}} - V_{DS5_{sat}} - \max{(|V_{T01}|)} \qquad \min{(V_{in})} = V_{SS} + \sqrt{\frac{I_5}{\beta_3}} + \max{(V_{T03})} - \min{(|V_{T01}|)}$$

Σχεδίαση τελεστικού ενισχυτή με είσοδο n-MOS

$$SR = \frac{I_5}{C_C} \qquad A_{v1} = \frac{-g_{m1}}{g_{ds2} + g_{ds4}} = \frac{-2g_{m1}}{I_5 \cdot (\lambda_2 + \lambda_4)} \qquad A_{v2} = \frac{-g_{m6}}{g_{ds6} + g_{ds7}} = \frac{-g_{m6}}{I_6 \cdot (\lambda_6 + \lambda_7)}$$

$$GB = \frac{g_{m1}}{C_C} \qquad p_2 = \frac{-g_{m6}}{C_L} \qquad Z = \frac{g_{m6}}{C_C} \qquad \beta = k' \frac{W}{L} \cong \mu_0 C_{ox} \frac{W}{L} \left(A/V^2 \right)$$

$$C_C > 0.22C_L \qquad I_5 = SR \cdot C_C \qquad S_3 = \left(\frac{W}{L} \right)_3 = \frac{I_5}{k'_3 \left[V_{DD} - \max\left(V_{in} \right) - \max\left(|V_{T03}| \right) + \min\left(V_{T01} \right) \right]^2}$$

$$\frac{g_{m3}}{2C_{gs3}} > 10 \cdot GB \qquad g_{m1} = GB \cdot C_C \Longrightarrow S_1 = S_2 = \frac{g_{m2}^2}{k'_2 I_5}$$